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PPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
09/954,864	09/17/2001	Satyadev R. Patel	P68-US	8736
26148	7590 08/18/2005		EXAM	INER
REFLECTI	VITY, INC. RO AVENUE		OLSEN, A	LLAN W
	E, CA 94085		ART UNIT	PAPER NUMBER
			1763	

DATE MAILED: 08/18/2005

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Serial No.: 09954864

Applicant: Satyadev R. Patel Filing Date: September 17, 2001 Date Mailed: August 18, 2005

ACKNOWLEDGEMENT OF REQUEST

Notice of Allowance/Allowability Mailed

The request for a copy of the initialed PTO 1449, dated March 25, 2005 , has been received by the U.S. Patent and Trademark Office.

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Natarsha Horne

For the Office of Patent Publication

Rev.02/24/05

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MEGE	18.6 A TIO			Application Number	09/954,884		
			CLOSURE	Filing Date	9/17/01		
STAT	STATEMENT BY APPLICANT			First Named Inventor	Patel		
				Art Unit	1763		
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Sheet	1	of	6	Altomey Docket Number	P68-US		

			U.S. PAT	ENT DOCUMENTS	
Examiner Initiats		Document Mumber Number - Kind Code ² (# Incom	Publication Date	Name of Patenties or Applicant of Clad Document	Pages, Columns, Lines, Where Relovant Passages or Relevant Floures Appear
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Application Number	09/954.864			
Filing Date	9/17/01			
First Named Inventor	Patel			
Art Unit	1783			
Examiner Name	Olsen, Allan			
Atterney Docket Number	P68-US			

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Examiner Initials		Occument Number Number - Kind Code ² (# known	Publication Date MM-QD-YYYY	Name of Pelantoe or Applicant of Cited Document	Pages, Columns, Unes, Where Relevant Passages or Relevant Figures Appear
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حبيلا	Ľ	JP-1986/61181131-A	08-13-1986	Shiniji et at.		

Date Considered Examiner Signature

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet of

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Application Number	09/954,864				
Filing Date	9/17/01				
First Named Inventor	Patel				
Art Unit	1763				
Examiner Name	Olsen, Allen				
Attorney Docket Number	P68-US				

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[&]quot;EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered, include copy of this form with next communication to applicant.

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Complete If Known Substitute for form 1449B/PTO 09/954,864 **Application Number** INFORMATION DISCLOSURE 9/17/01 Filing Date First Named Inventor Patei STATEMENT BY APPLICANT Group Art Unit 1763 Examiner Name Olsen, Allan (use as many sheets as necessary) P68-US Attorney Docket Number Sheet of

		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS .						
Examiner Initials	Cita No.1	include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s) multisher of						
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Examiner Signature	Alla Olan	Date Considered	3-7-05

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				Application Number	09/954,884	
INFOR	NOITANS	I DIS	CLOSURE	Filing Date	9/17/01	
STATI	EMENT R	Y A	PPLICANT	First Named Inventor	Petel	
10.7"	-141-141 F	,, <u>,</u>		Group Art Unit	1763	
	(use as many st	heets a	1 necessary)	Examiner Name	Olzen, Allan	
Sheet	6	of	6	Attorney Docket Number	P68-US	

		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS	
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